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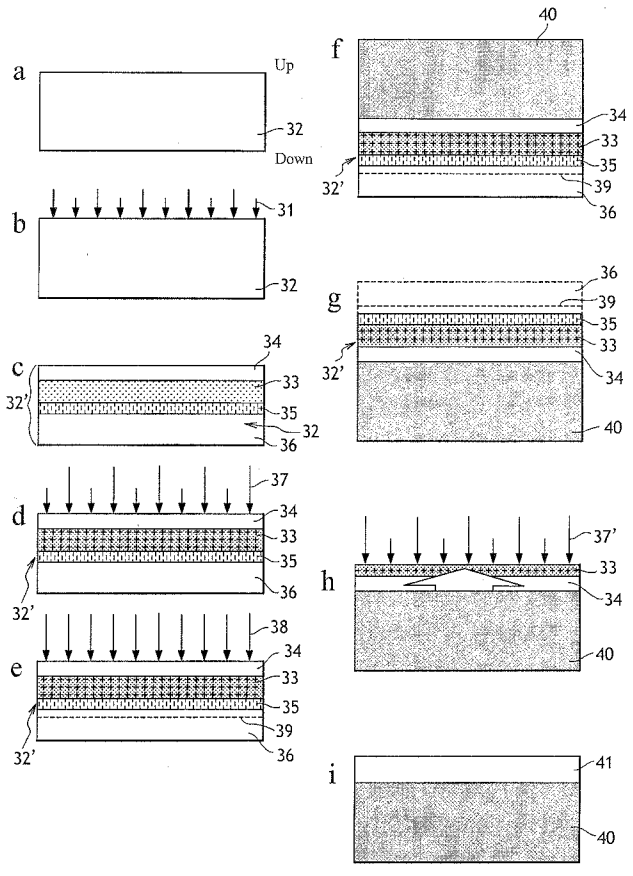
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[Continued on next page]

(54) **Title:** METHOD FOR MAKING A STRUCTURE COMPRISING AT LEAST ONE THIN LAYER IN AN AMORPHOUS MATERIAL OBTAINED BY EPITAXY ON A SUPPORTING SUBSTRATE AND STRUCTURE OBTAINED ACCORDING TO SAID METHOD



(57) **Abstract:** The present invention relates to a method for making a structure comprising at least one thin layer on a supporting substrate, remarkable in that it includes at least steps for forming from said supporting substrate a so-called intermediate structure comprising an amorphous layer, a first crystalline layer containing point defects and located immediately underneath said amorphous layer, a second crystalline layer located in the lower portion of the intermediate structure; bonding a receiving substrate on the upper face of said intermediate structure; removing the layer of the intermediate structure in which point defects have formed so that amorphous layer forms the upper layer of the intermediate structure. Another object of the invention relates to a substrate comprising at least one thin layer in an amorphous material on a supporting substrate, remarkable in that it comprises a receiving substrate, a central crystalline layer and an amorphous layer, said receiving substrate, the crystalline layer and the amorphous layer not having any EOR type point defect.

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